

N-channel TrenchMOS logic level FET Rev. 04 — 8 July 2010

Product data sheet

Suitable for logic level gate drive

Switched-mode power supplies

sources

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

Simple gate drive required due to low gate charge

1.3 Applications

DC-to-DC convertors

1.4 Quick reference data

Quick reference data Table 1

Table 1.	Quick reference da	la				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	43.4	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	57.6	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 9}}; \\ \text{see } \underline{\text{Figure 10}} \end{array}$	-	14	17	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge		-	2.9	-	nC

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source ^[1]		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PHP36N03LT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

I_{SM}

173.6 A

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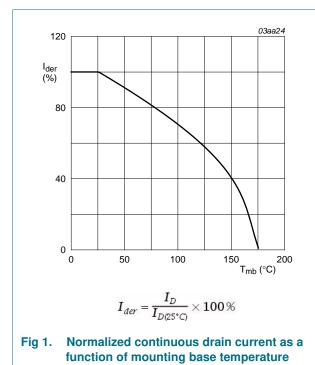
4. Limiting values

Table 4. Limiting values

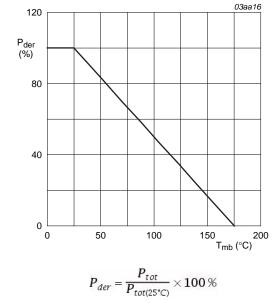
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
gate-source voltage		-20	20	V
drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	30.7	А
	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	43.4	A
peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	173.6	А
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	57.6	W
storage temperature		-55	175	°C
junction temperature		-55	175	°C
diode				
source current	T _{mb} = 25 °C	-	43.4	А
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature diode	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} \\ \mbox{drain-gate voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C}; \ R_{GS} = 20 \ k\Omega \\ \mbox{gate-source voltage} \\ \mbox{drain current} & V_{GS} = 10 \ V; \ T_{mb} = 100 \ {}^\circ\mbox{C}; \ see \ Figure 1} \\ \ V_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 1}; \\ \ see \ Figure 3 \\ \mbox{pulsed}; \ t_p \leq 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \\ \ see \ Figure 3 \\ \ total \ power \ dissipation \\ \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2 \\ \ storage \ temperature \\ \ junction \ temperature \\ \ diode \\ \end{array}$	$\begin{array}{c c c c c c } \mbox{drain-source voltage} & T_j \geq 25 \ {}^\circ\mbox{C}; \ T_j \leq 175 \ {}^\circ\mbox{C} & - & & & & & & & & & & & & & & & & & $	$\begin{array}{cccc} drain-source \ voltage & T_j \geq 25\ ^{\circ}C;\ T_j \leq 175\ ^{\circ}C & - & 30 \\ drain-gate \ voltage & T_j \geq 25\ ^{\circ}C;\ T_j \leq 175\ ^{\circ}C;\ R_{GS} = 20\ k\Omega & - & 30 \\ gate-source \ voltage & -20 & 20 \\ drain\ current & V_{GS} = 10\ V;\ T_{mb} = 100\ ^{\circ}C;\ see\ Figure\ 1 & - & 30.7 \\ V_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1; & - & 43.4 \\ see\ Figure\ 3 & - & - & 43.4 \\ see\ Figure\ 3 & - & - & 173.6 \\ see\ Figure\ 3 & - & - & 57.6 \\ storage\ temperature & T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 2 & - & 57.6 \\ storage\ temperature & -55 & 175 \\ junction\ temperature & -55 & 175 \\ \end{array}$

pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$



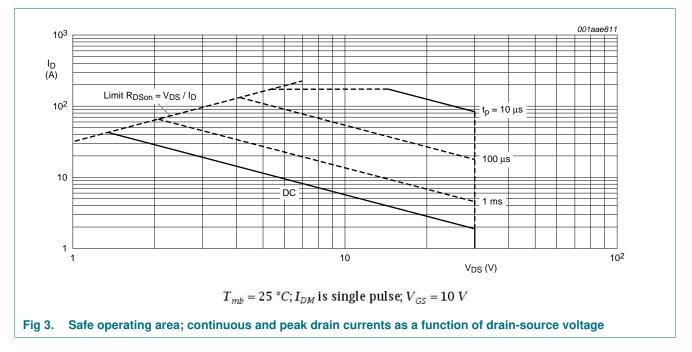
peak source current





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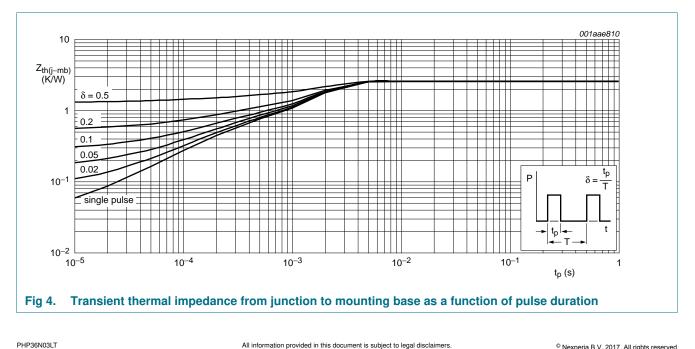
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Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th}(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	2.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



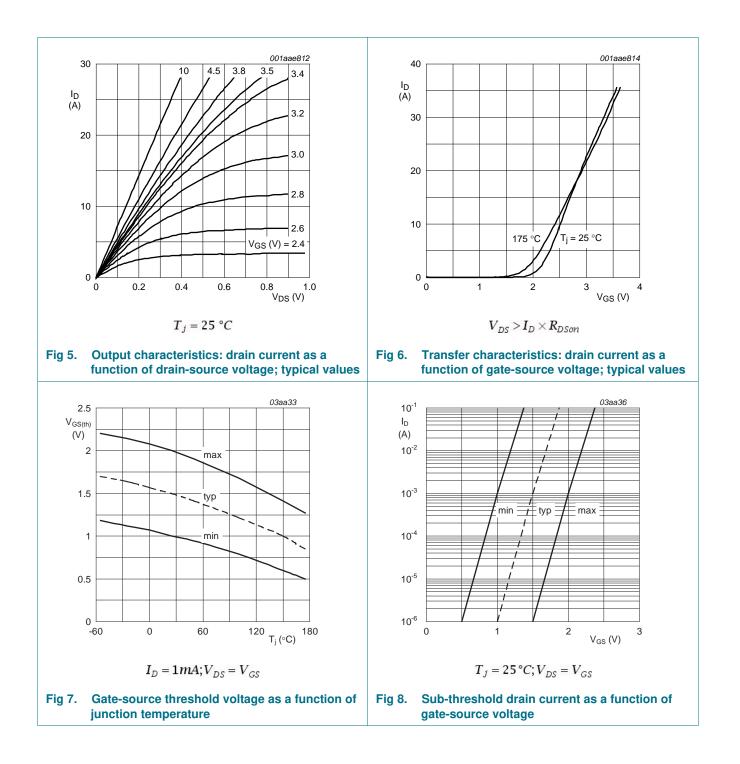
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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = 175 \ ^\circ\text{C};$ see <u>Figure 7</u> ; see <u>Figure 8</u>	0.5	-	-	V
		$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = 25 \ ^{\circ}\text{C};$ see <u>Figure 7</u> ; see <u>Figure 8</u>	1	1.5	2	V
		I _D = 250 μA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	2.2	V
I _{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
Boom	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	14	17	mΩ
		V _{GS} = 4.5 V; I _D = 12 A; T _j = 175 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	- 32.4	39.6	mΩ
		V _{GS} = 3.5 V; I _D = 5.2 A; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	22	40	mΩ
		V_{GS} = 4.5 V; I_D = 12 A; T_j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	18	22	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 36 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$	-	18.5	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 12}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	4.2	-	nC
Q _{GD}	gate-drain charge		-	2.9	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; see <u>Figure 13</u>	-	690	-	pF
C _{oss}	output capacitance	V _{DS} = 0 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; see <u>Figure 13</u>	-	160	-	pF
C _{rss}	reverse transfer capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; see <u>Figure 13</u>	-	110	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; \text{ R}_{L} = 0.6 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	10	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns
t _f	fall time		-	19	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 14</u>	-	0.97	1.2	V

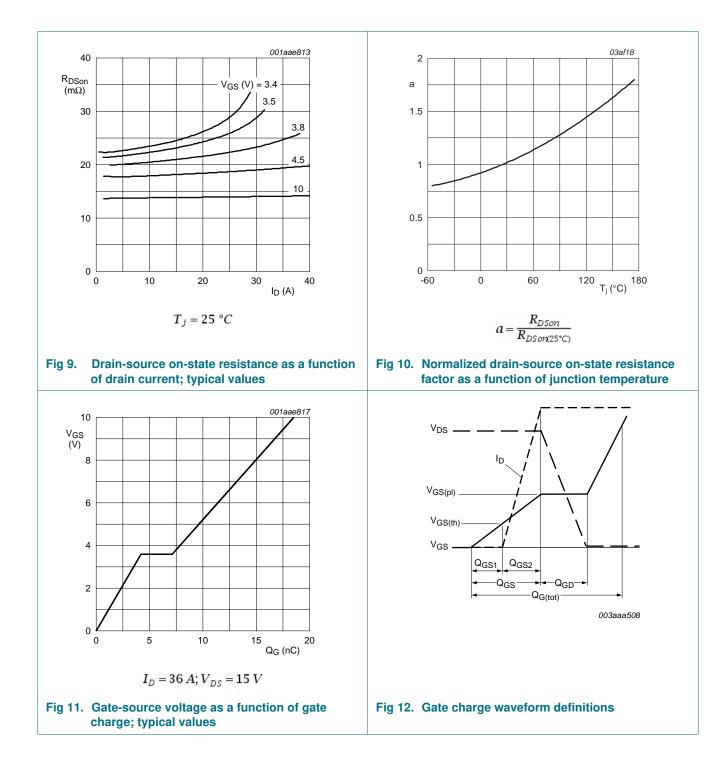
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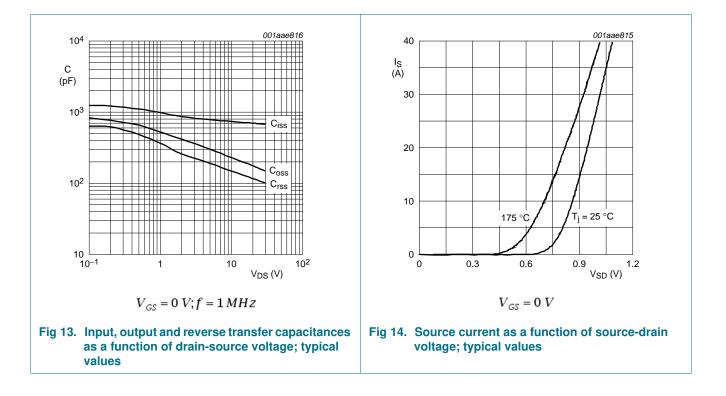
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Package outline 7.

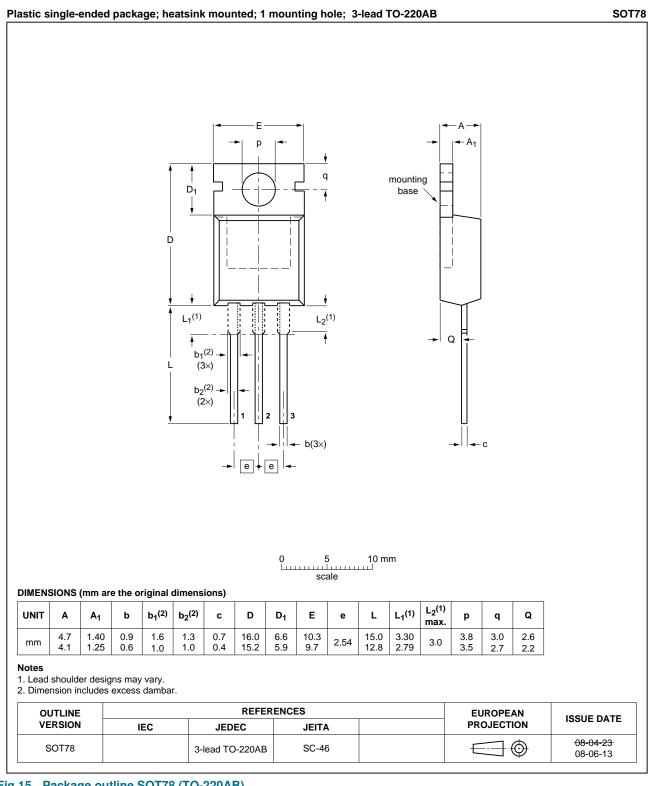


Fig 15. Package outline SOT78 (TO-220AB)

PHP36N03LT **Product data sheet**

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8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP36N03LT v.4	20100708	Product data sheet	-	PHP36N03LT v.3
Modifications:	 Various changes 	s to content.		
PHP36N03LT v.3	20100329	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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